

# MMBT3904LP-7B Datasheet



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DiGi Electronics Part Number MMBT3904LP-7B-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number MMBT3904LP-7B

Description TRANS NPN 40V 0.2A 3DFN

Detailed Description Bipolar (BJT) Transistor NPN 40 V 200 mA 300MHz 2

50 mW Surface Mount X1-DFN1006-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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## **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
Manufacturer Froduct Number.	
MMBT3904LP-7B	Diodes Incorporated
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN	200 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
40 V	300mV @ 5mA, 50mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
	100 @ 10mA, 1V
Power - Max:	Frequency - Transition:
250 mW	300MHz
Operating Temperature:	Grade:
-55°C ~ 150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Package / Case:	Supplier Device Package:
3-UFDFN	X1-DFN1006-3
Base Product Number:	
MMBT3904	

## **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

8541.21.0075





#### 40V NPN SMALL SIGNAL TRANSISTOR IN DFN1006-3

#### **Features**

- BV<sub>CEO</sub> > 40V
- I<sub>C</sub> = 200mA High Collector Current
- P<sub>D</sub> = 1000mW Power Dissipation
- 0.60mm<sup>2</sup> Package Footprint, 13 Times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary PNP Type: MMBT3906LP
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

 $\underline{\text{https://www.diodes.com/products/automotive/automotive-products/.}}$ 

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

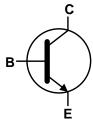
### **Mechanical Data**

- Package: X1-DFN1006-3
- Package Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0008 grams (Approximate)

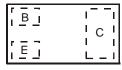
X1-DFN1006-3



**Bottom View** 



Device Symbol



Top View Device Schematic

#### **Ordering Information** (Note 4)

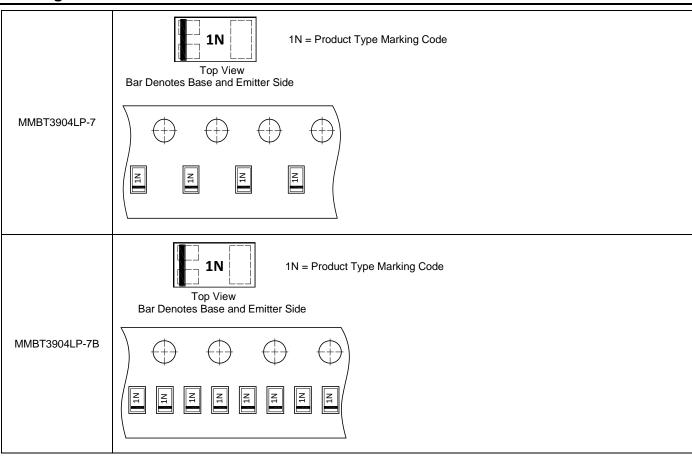
Orderable Part	rderable Part Package Marking Reel Size (inches)		Tape Width (mm)	Packing		
Number	i ackage	Warking	ixeei Size (iliches)	Tape Width (IIIII)	Qty.	Carrier
MMBT3904LP-7	X1-DFN1006-3	1N	7	8	3,000	Reel
MMBT3904LP-7B	X1-DFN1006-3	1N	7	8	10,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



### **Marking Information**





## **Absolute Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current	Ic	200	mA
Peak Collector Current	I <sub>CM</sub>	200	mA

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Dawar Dissination	(Note 5)	D	400	m\\/	
Power Dissipation	(Note 6)	P <sub>D</sub>	1000	mW	
The second Decision of the Austrian	(Note 5)	D	310	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	120		
Thermal Resistance, Junction to Lead (Note 7)		$R_{ heta JL}$	120	°C/W	
Operating and Storage and Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

Notes:

<sup>5.</sup> For the device mounted on minimum recommended pad layout 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition.

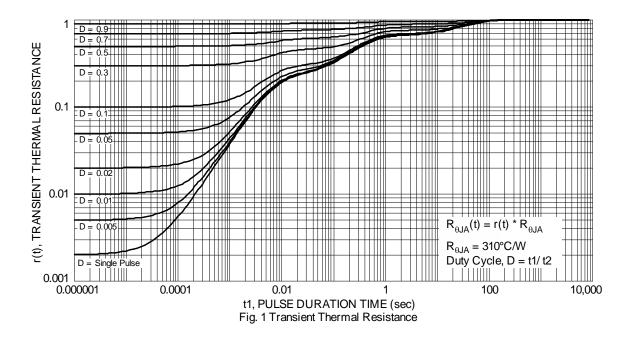
<sup>6.</sup> Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.

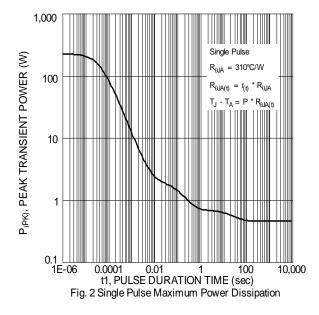
<sup>7.</sup> Thermal resistance from junction to solder-point (on the exposed collector pad).

<sup>8.</sup> Refer to JEDEC specification JESD22-A114 and JESD22-A115.



#### **Thermal Characteristics**







### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

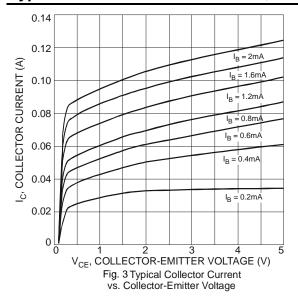
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60	_	V	$I_C = 10\mu A, I_E = 0A$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	40	_	V	$I_C = 1.0 \text{mA}, I_B = 0 \text{A}$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6.0	_	V	$I_E = 10\mu A, I_C = 0A$
Collector Cutoff Current	I <sub>CEX</sub>	_	50	nA	$V_{CE} = 30V, V_{EB(off)} = 3.0V$
Base Cutoff Current	$I_{BL}$	_	50	nA	$V_{CE} = 30V, V_{EB(off)} = 3.0V$
ON CHARACTERISTICS (Note 9)					
		40	_		$I_C = 100\mu A, V_{CE} = 1.0V$
		70	_		$I_C = 1.0 \text{mA}, V_{CE} = 1.0 \text{V}$
DC Current Gain	h <sub>FE</sub>	100	300	_	$I_C = 10mA, V_{CE} = 1.0V$
		60	_		I <sub>C</sub> = 50mA, V <sub>CE</sub> = 1.0V
		30	_		I <sub>C</sub> = 100mA, V <sub>CE</sub> = 1.0V
Collector Emitter Seturation Voltage	V		0.20	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_	0.30	V	I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA
Base Emitter Caturation Voltage	V <sub>BE(sat)</sub>	0.65	0.85	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA
Base-Emitter Saturation Voltage			0.95	V	$I_C = 50mA$ , $I_B = 5.0mA$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	$C_{obo}$		4.0	pF	$V_{CB} = 5.0V$ , $f = 1.0MHz$ , $I_E = 0A$
Input Capacitance	C <sub>ibo</sub>		8.5	pF	$V_{EB} = 0.5V$ , $f = 1.0MHz$ , $I_{C} = 0A$
Input Impedance	h <sub>ie</sub>	1.0	10	kΩ	
Voltage Feedback Ratio	h <sub>re</sub>	0.5	8.0	x 10 <sup>-4</sup>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA
Small Signal Current Gain	h <sub>fe</sub>	100	400	_	f = 1.0kHz
Output Admittance	hoe	1.0	40	μs	
Current Gain-Bandwidth Product	f⊤	300	_	MHz	V <sub>CE</sub> = 20V, I <sub>C</sub> = 10mA f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t <sub>d</sub>	-	35	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA
Rise Time	t <sub>r</sub>	_	35	ns	$V_{BE(off)} = 0.5V, I_{B1} = 1.0mA$
Storage Time	ts	_	200	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA
Fall Time	t <sub>f</sub>		50	ns	$I_{B1} = -I_{B2} = 1.0 \text{mA}$

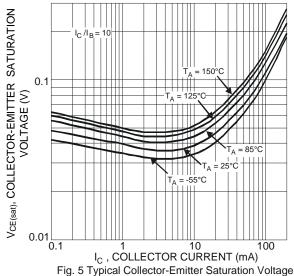
Note:

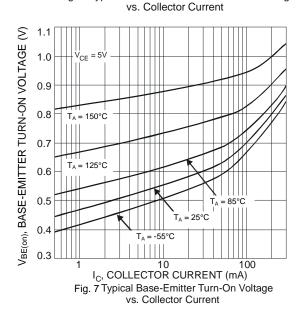
<sup>9.</sup> Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

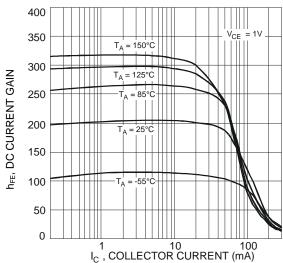


#### Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

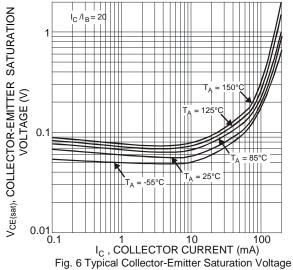








 $\rm I_{\rm C}$  , COLLECTOR CURRENT (mÅ) Fig. 4 Typical DC Current Gain vs. Collector Current



vs. Collector Current

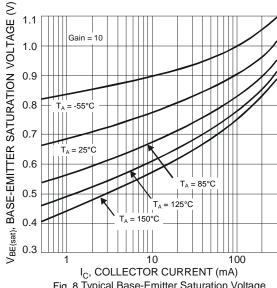


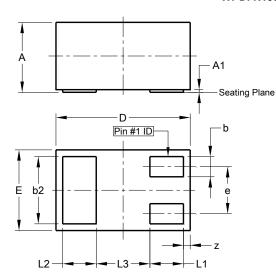
Fig. 8 Typical Base-Emitter Saturation Voltage vs. Collector Current



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X1-DFN1006-3

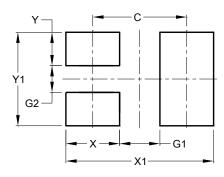


Х	X1-DFN1006-3					
Dim	Min	Max	Тур			
Α	0.47	0.53	0.50			
A1	0.00	0.05	0.03			
b	0.10	0.20	0.15			
b2	0.45	0.55	0.50			
D	0.95	1.075	1.00			
Е	0.55	0.675	0.60			
е	ı	-	0.35			
L1	0.20	0.30	0.25			
L2	0.20	0.30	0.25			
L3	-	-	0.40			
z	0.02	0.08	0.05			
All Dimensions in mm						

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X1-DFN1006-3



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70



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